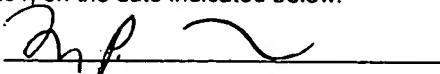


Docket No.: L&L-I0232

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231, on the date indicated below.

By: 

Date: April 1, 2002

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant : Wolfgang Rösner et al.  
Applic. No. : 10/047,013  
Filed : January 16, 2002  
Title : Method for Producing a Vertical Semiconductor Transistor Component and Vertical Semiconductor Transistor Component  
Art Unit : 2811

**INFORMATION DISCLOSURE STATEMENT**

Hon. Commissioner of Patents and Trademarks,  
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

United States Patent No. 5,714,766 (Chen et al.), dated February 3, 1998;

German Patent DE 196 32 835 C1 (Schäfer et al.), dated April 2, 1998, method for producing a capacitor in a semiconductor configuration;

European Patent Application EP 0 843 361 A1 (Nakazato et al.), dated May 20, 1998;

H.I. Liu et al.: "Self-limiting oxidation for fabricating sub-5 nm silicon nanowires", Appl. Phys. Lett., Vol. 64, No. 11, March 14, 1994, pp. 1383-1385;

Harald Gossner et al.: "Vertical Si-Metal-Oxide-Semiconductor Field Effect Transistors with Channel Lengths of 50 nm by Molecular Beam Epitaxy", Jpn. J. Appl. Phys., Vol. 33, 1994, pp. 2423-2428;

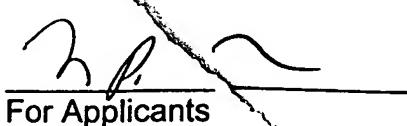
Lothar Risch et al.: "Vertical MOS Transistors with 70 nm Channel Length", IEEE Transactions on Electron Devices, Vol. 43, No. 9, September 1996, pp. 1495-1498;

Hiroshi Fukuda et al.: "Fabrication of silicon nanopillars containing polycrystalline silicon/insulator multilayer structures", Appl. Phys. Lett., Vol. 70, No. 3, January 20, 1997, pp. 333-335;

Hiroshi Mizuta et al.: "High-speed single-electron memory: cell design and architecture", XP-002151823, IEEE 1998, pp. 67-72.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,

  
For Applicants

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Reg. No. 43,248

Date: April 1, 2002

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